09/943,196

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of claims

Claims 1-5. (canceled)

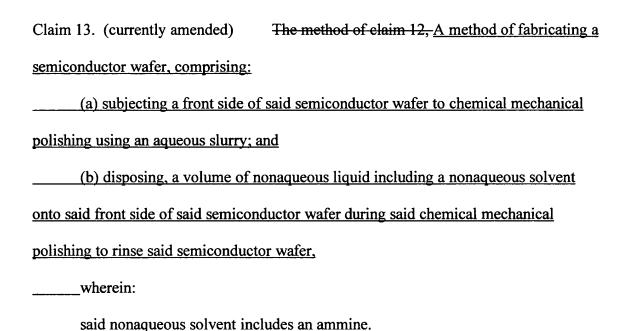
Claim 6. (previously presented) The method of claim 23, wherein:

said weight % of said nonaqueous solvent in said aqueous slurry/nonaqueous solvent mixture is increased until said aqueous slurry/nonaqueous solvent mixture is substantially free of said aqueous slurry.

- Claim 7. (currently amended) The method of claim <u>25</u>[[1]], wherein: said nonaqueous solvent includes an ammine.
- Claim 8. (currently amended) The method of claim <u>25</u>[[1]], wherein: said nonaqueous solvent includes dimethylsulfoxide.
- Claim 9. (currently amended) The method of claim <u>25</u>[[1]], wherein: said nonaqueous solvent includes N,N-propanalamide.
- Claim 10. (currently amended) The method of claim <u>25</u>[[1]], wherein: said nonaqueous solvent includes analine.

Claim 11. (currently amended) The method of claim <u>25</u>[[1]], wherein: said nonaqueous solvent includes N,N-dimethlyanaline.

Claim 12. (canceled)



Claims 14-20. (canceled)

- Claim 21. (previously presented) A method of fabricating a semiconductor wafer, comprising:
- (a) mixing an aqueous slurry containing an abrasive material and a nonaqueous solvent in a mixing unit so as to create a first volume of an aqueous slurry/nonaqueous solvent mixture with a first weight % of said nonaqueous solvent prior to being disposed onto said semiconductor wafer;

(b) disposing said first volume of the aqueous slurry/nonaqueous solvent mixture containing an abrasive material onto said a semiconductor wafer;

- (c) polishing the semiconductor wafer with a polishing pad using said first volume;
- (d) mixing said aqueous slurry containing an abrasive material and said nonaqueous solvent so as to create a second volume of an aqueous slurry/nonaqueous solvent mixture having a greater weight % of said nonaqueous solvent than said first weight % prior to being disposed onto said semiconductor wafer;
- (e) disposing said second volume of said aqueous slurry/nonaqueous solvent mixture containing an abrasive material onto said semiconductor wafer;
 and
 - (f) polishing said semiconductor wafer using said second volume.
- Claim 22. (previously presented) The method of claim 21, further comprising: reducing the pressure of said polishing pad on said semiconductor wafer after disposing said first volume of said aqueous slurry/nonaqueous solvent mixture onto said semiconductor wafer and before completing disposing said second volume of said aqueous slurry/nonaqueous solvent mixture onto said semiconductor wafer.
- Claim 23. (previously presented) The method of claim 21, wherein said disposing said second volume of aqueous slurry/nonaqueous solvent mixture further comprises:

disposing said second volume of aqueous slurry/nonaqueous solvent mixture during said polishing of said semiconductor wafer.

Claim 24. (previously presented) The method of claim 23, wherein mixing said second volume of an aqueous slurry/nonaqueous solvent mixture is performed at least partially simultaneously with disposing said first volume onto said semiconductor wafer, and mixing said second volume comprises:

controlling a flow of said nonaqueous solvent into said mixing unit.

Claim 25. (currently amended) The method of claim 3, further comprising: A method of fabricating a semiconductor wafer, comprising:

- (a) disposing a volume of an aqueous slurry containing an abrasive material onto a semiconductor wafer and polishing the semiconductor wafer with a polishing pad, said polishing pad in contact with said semiconductor wafer when said volume of nonaqueous liquid is disposed onto said semiconductor wafer; and
- (b) disposing a volume of nonaqueous liquid including a nonaqueous solvent onto said semiconductor wafer to rinse the semiconductor wafer.
- (c) reducing the pressure of said polishing pad on said semiconductor wafer prior to completing disposing a volume of nonaqueous liquid including a nonaqueous solvent onto said semiconductor wafer.

Claim 26. (currently amended) The method of claim [[12]]13, further comprising:

reducing the pressure of a polishing pad on said front side of said semiconductor wafer prior to completing disposing a volume of nonaqueous liquid including a nonaqueous solvent onto said front side of said semiconductor wafer.